STL8N10F7

N-channel 100 V, 17 mΩ typ., 8 A STripFET™ F7 Power MOSFET in a PowerFLAT™ 3.3x3.3 package

Datasheet - production data

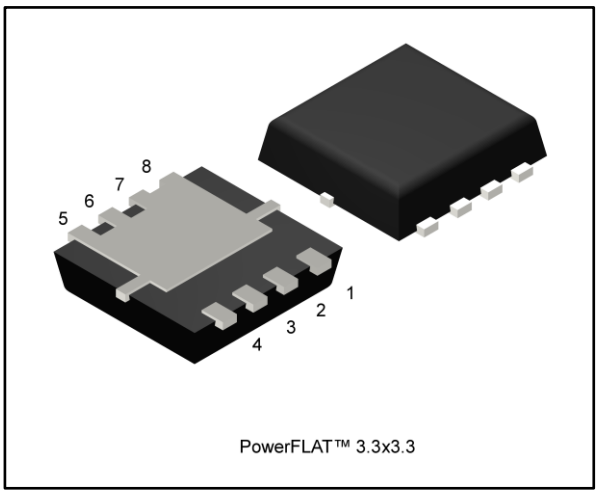
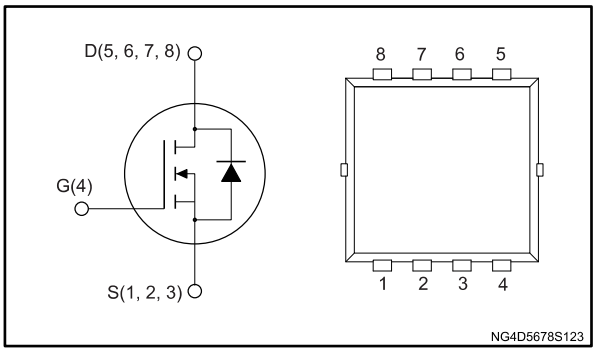


Figure 1: Internal schematic diagram



Features

Order code	V_{DS}	$R_{DS(on)}$ max.	I_D	P_{TOT}
STL8N10F7	100 V	20 mΩ	8 A	2.9 W

- Among the lowest $R_{DS(on)}$ on the market
- Excellent FoM (figure of merit)
- Low C_{rss}/C_{iss} ratio for EMI immunity
- High avalanche ruggedness

Applications

- Switching applications

Description

This N-channel Power MOSFET utilizes STripFET™ F7 technology with an enhanced trench gate structure that results in very low on-state resistance, while also reducing internal capacitance and gate charge for faster and more efficient switching.

Table 1: Device summary

Order code	Marking	Package	Packing
STL8N10F7	8N10F	PowerFLAT™ 3.3x3.3	Tape and reel

Contents

1 Electrical ratings

Table 2: Absolute maximum ratings

Symbol	Parameter	Value	Unit
V_{DS}	Drain-source voltage	100	V
V_{GS}	Gate-source voltage	±20	V
I_D(1)	Drain current (continuous) at T_{pcb} = 25 °C	8	A
I_D(1)	Drain current (continuous) at T_{pcb}= 100 °C	6	A
I_D(2)	Drain current (continuous) at T_c = 25 °C	35	A
I_D(2)	Drain current (continuous) at Tc= 100 °C	22	A
I_{DM}(1)(3)	Drain current (pulsed)	32	A
I_{DM}(2)(3)	Drain current (pulsed)	140	A
P_{TOT}(2)	Total dissipation at T_C = 25 °C	50	W
P_{TOT}(1)	Total dissipation at T_{pcb} = 25 °C	2.9	W
T_{stg}	Storage temperature range	-55 to 150	°C
T_j	Operating junction temperature range		°C

Notes:

(1)This value is rated according to $R_{thj\text{-}pcb}$.

(2)This value is rated according to $R_{thj\text{-}case}$.

(3)Pulse width limited by safe operating area.

Table 3: Thermal data

Symbol	Parameter	Value	Unit
$R_{thj\text{-}case}$	Thermal resistance junction-case	2.5	°C/W
$R_{thj\text{-}pcb}$(1)	Thermal resistance junction-pcb	42.8	

Notes:

(1)When mounted on FR-4 board of 1inch², 2oz Cu, t < 10 s.

2 Electrical characteristics

(T_C= 25 °C unless otherwise specified)

Table 4: Static

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$V_{(BR)DSS}$	Drain-source breakdown voltage	V_{GS} = 0 V, I_D = 1 mA	100			V
I_{DSS}	Zero gate voltage drain current	V_{GS} = 0 V, V_{DS} = 100 V			1	µA
		V_{GS} = 0 V, V_{DS} = 100 V, T_c = 125 °C (1)			100	µA
I_{GSS}	Gate-body leakage current	V_{DS} = 0 V, V_{GS} = ±20 V			±100	nA
$V_{GS(th)}$	Gate threshold voltage	V_{DS} = V_{GS}, I_D = 250 µA	2.5		4.5	V
$R_{DS(on)}$	Static drain-source on-resistance	V_{GS} = 10 V, I_D = 4 A		17	20	mΩ

Notes:

(1)Defined by design, not subject to production test.

Table 5: Dynamic

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
C_{iss}	Input capacitance	V_{DS}= 50 V, f = 1 MHz, V_{GS} = 0 V	-	1640	-	pF
C_{oss}	Output capacitance		-	360	-	pF
C_{rss}	Reverse transfer capacitance		-	25	-	pF
Q_g	Total gate charge	V_{DD} = 50 V, I_D = 8 A, V_{GS} = 0 to 10 V (see *Figure 14: "Test circuit for gate charge behavior"*)	-	25	-	nC
Q_{gs}	Gate-source charge		-	12	-	nC
Q_{gd}	Gate-drain charge		-	5	-	nC

Table 6: Switching times

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$	Turn-on delay time	V_{DD} = 50 V, I_D = 4 A, R_G = 4.7 Ω, V_{GS} = 10 V (see *Figure 13: "Test circuit for resistive load switching times"* and *Figure 18: "Switching time waveform"*)	-	15	-	ns
t_r	Rise time		-	17	-	ns
$t_{d(off)}$	Turn-off-delay time		-	24	-	ns
t_f	Fall time		-	8	-	ns

Table 7: Source-drain diode

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
V_{SD} (1)	Forward on voltage	V_{GS} = 0 V, I_{SD} = 8 A	-		1.1	V
t_{rr}	Reverse recovery time	I_{SD} = 8 A, di/dt = 100 A/µs, V_{DD} = 80 V, T_j = 150 °C (see *Figure 15: "Test circuit for inductive load switching and diode recovery times"*)	-	53		ns
Q_{rr}	Reverse recovery charge		-	67		nC
I_{RRM}	Reverse recovery current		-	2.5		A

Notes:

(1)Pulse test: pulse duration = 300 µs, duty cycle 1.5%

2.1 Electrical characteristics (curves)

Figure 2: Safe operating area

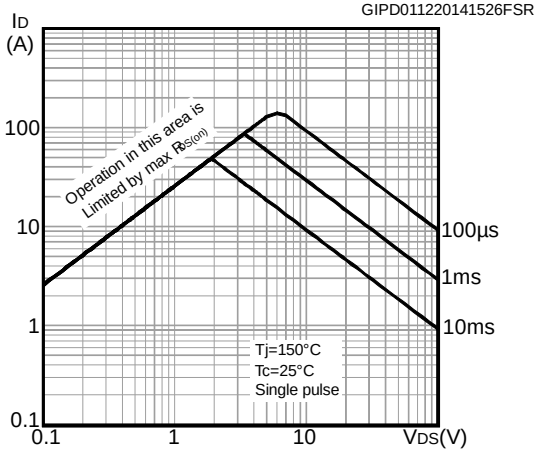


Figure 3: Thermal impedance

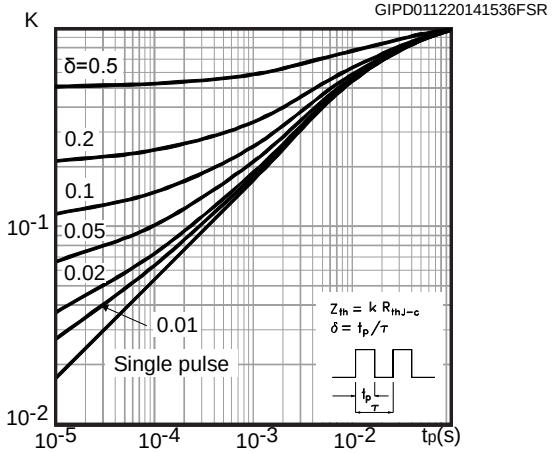


Figure 4: Output characteristics

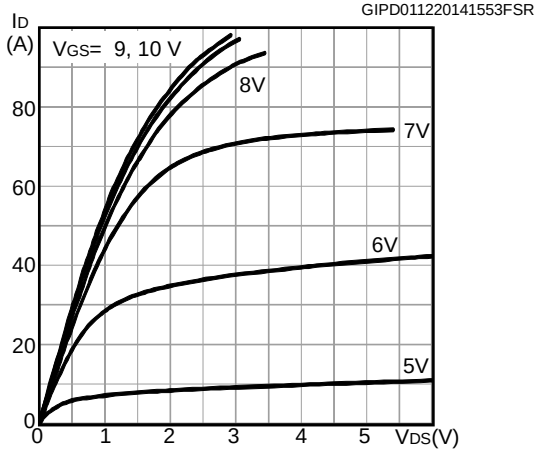


Figure 5: Transfer characteristics

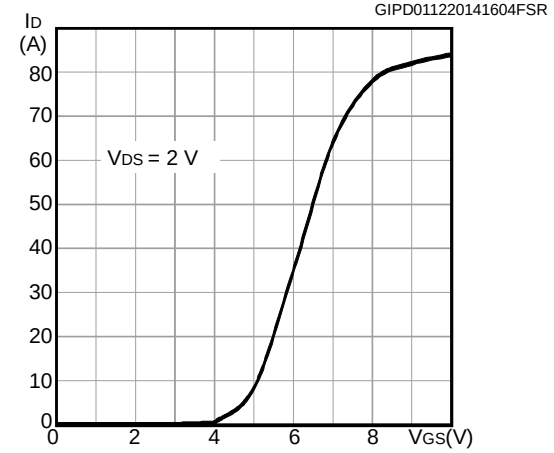


Figure 6: Gate charge vs gate-source voltage

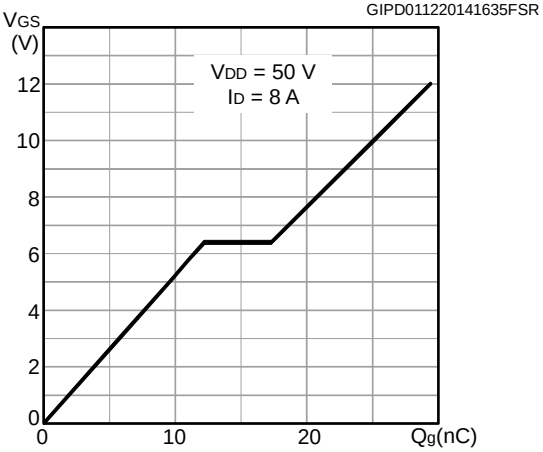


Figure 7: Static drain-source on-resistance

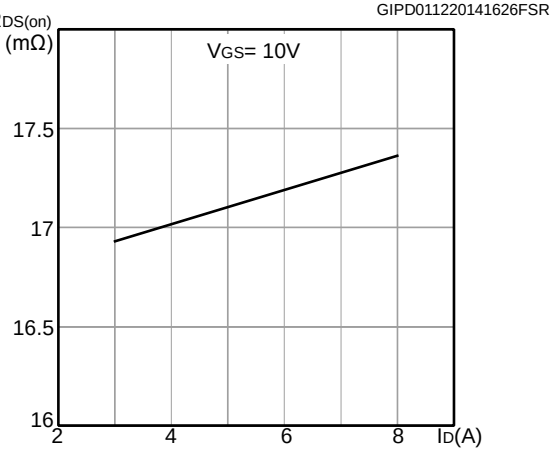


Figure 8: Capacitance variations

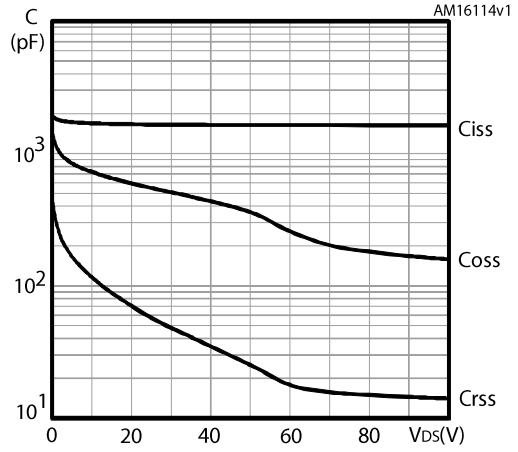


Figure 9: Normalized gate threshold voltage vs temperature

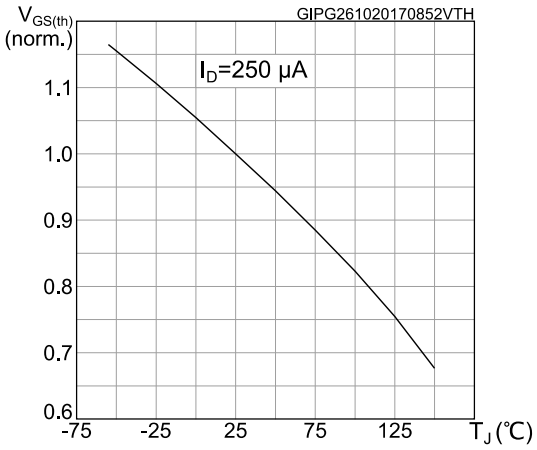


Figure 10: Normalized on-resistance vs temperature

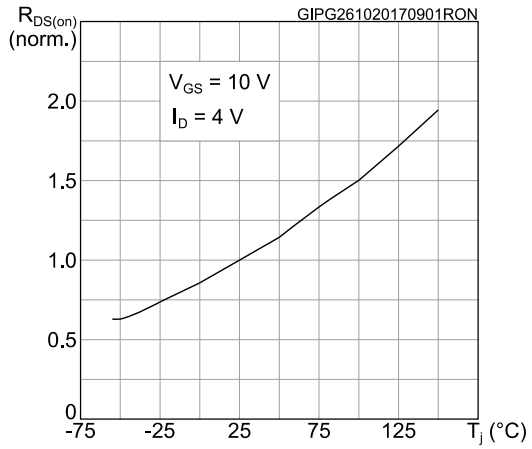


Figure 11: Normalized $V_{(BR)DSS}$ vs temperature

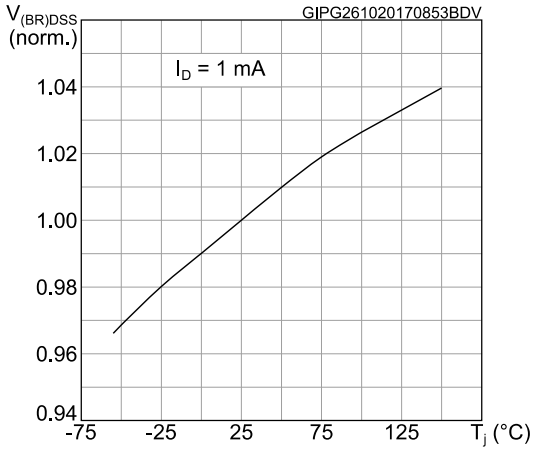
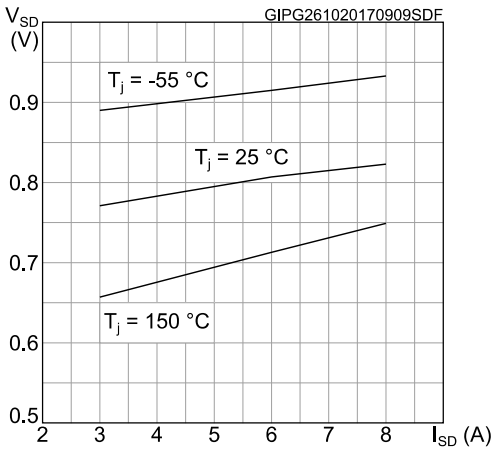


Figure 12: Source-drain diode forward characteristics



3 Test circuits

Figure 13: Test circuit for resistive load switching times

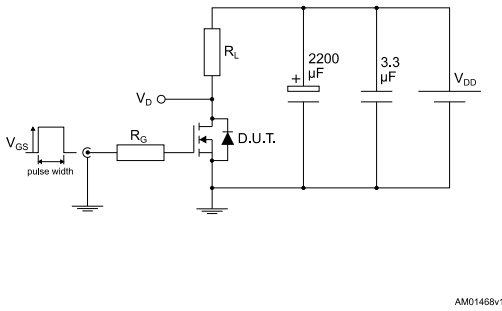


Figure 14: Test circuit for gate charge behavior

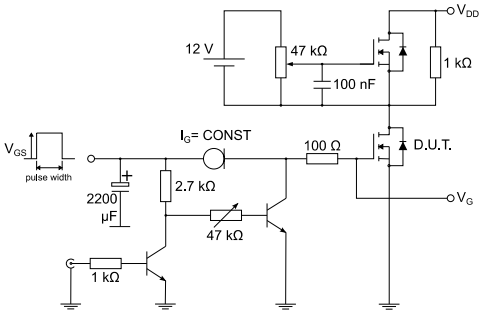


Figure 15: Test circuit for inductive load switching and diode recovery times

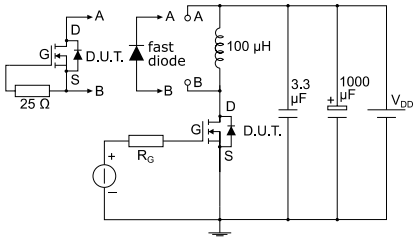


Figure 16: Unclamped inductive load test circuit

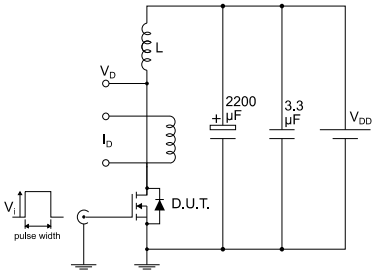


Figure 17: Unclamped inductive waveform

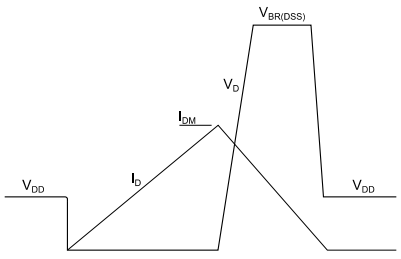
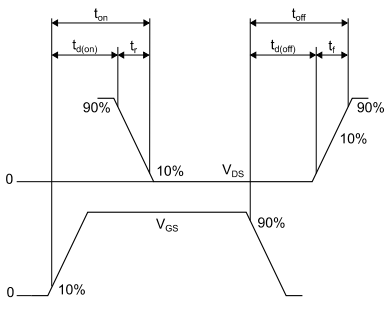


Figure 18: Switching time waveform



4 Package information

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK® packages, depending on their level of environmental compliance. ECOPACK® specifications, grade definitions and product status are available at: ***www.st.com***. ECOPACK® is an ST trademark.

4.1 PoweFLAT 3.3x3.3 pakage information

Figure 19: PowerFLAT™ 3.3x3.3 package outline

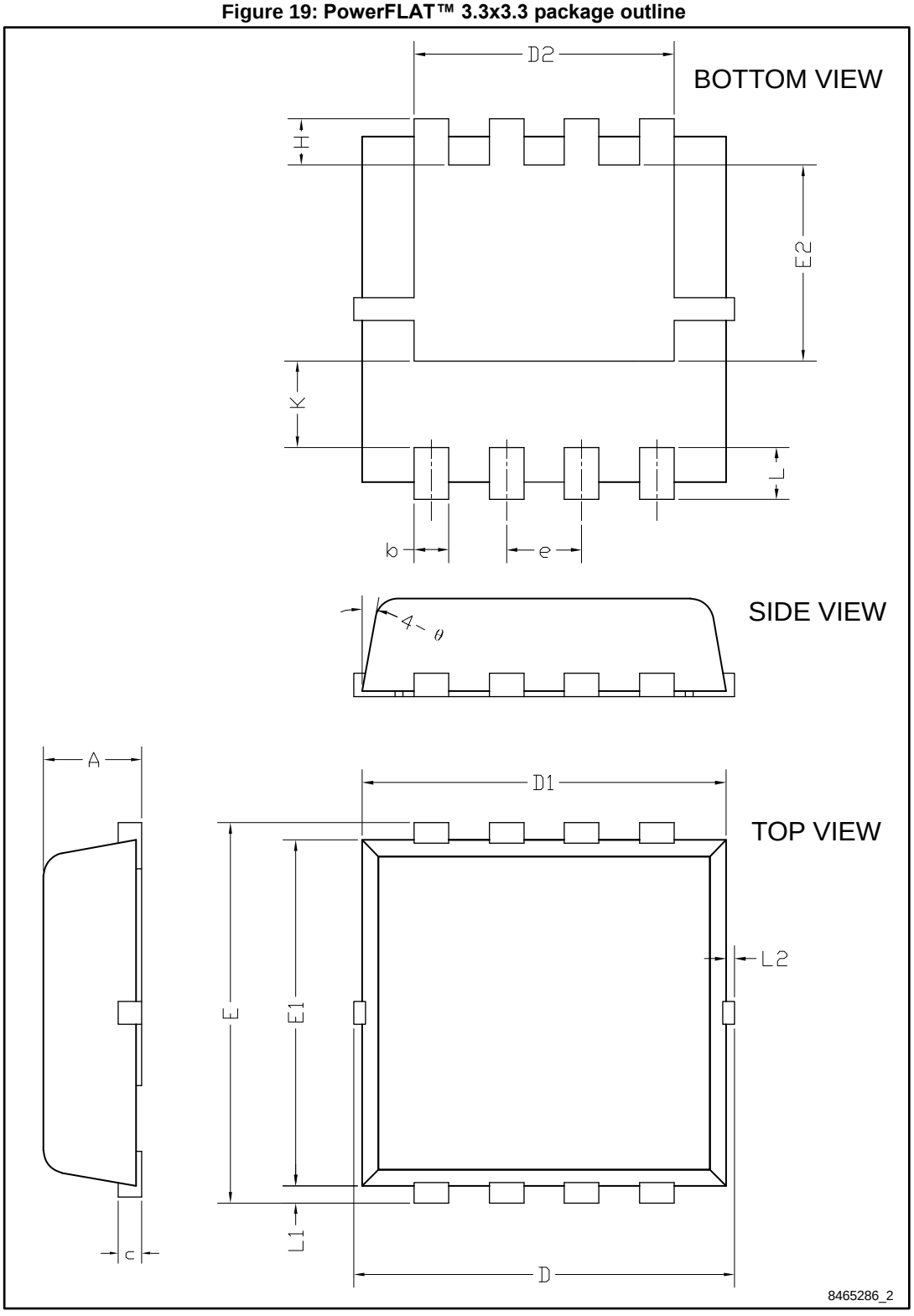
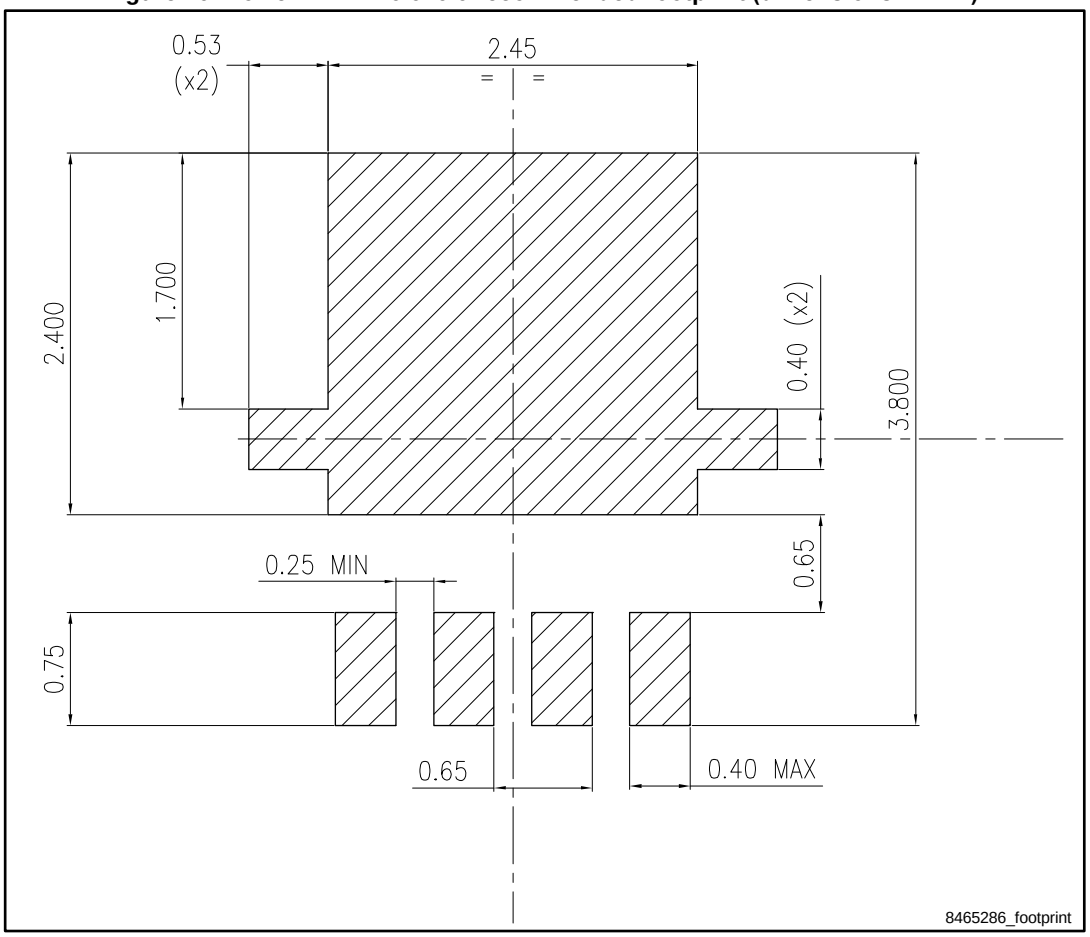


Table 8: PowerFLAT™ 3.3x3.3 package mechanical data

Dim.	mm		
	Min.	Typ.	Max.
A	0.70	0.80	0.90
b	0.25	0.30	0.39
c	0.14	0.15	0.20
D	3.10	3.30	3.50
D1	3.05	3.15	3.25
D2	2.15	2.25	2.35
e	0.55	0.65	0.75
E	3.10	3.30	3.50
E1	2.90	3.00	3.10
E2	1.60	1.70	1.80
H	0.25	0.40	0.55
K	0.65	0.75	0.85
L	0.30	0.45	0.60
L1	0.05	0.15	0.25
L2			0.15
θ	8°	10°	12°

Figure 20: PowerFLAT™ 3.3x3.3 recommended footprint (dimensions in mm)



5 Revision history

Table 9: Document revision history

Date	Revision	Changes
31-Jul-2013	1	First release.
05-Dec-2014	2	Document status promoted from preliminary to production data. Modified title, features and description in cover page. Modified: $R_{DS(on)}$ typical and max values in first page and in *Table 4: On/off states* Modified: *Section 4: Package mechanical data* Added *Section 2.1: Electrical characteristics (curves).*
02-Nov-2017	3	Datasheet promoted from preliminary data to production data. Modified title, silhouette and features table on cover page. Modified *Table 2: "Absolute maximum ratings"*, *Table 4: "Static"* and *Table 5: "Dynamic"*. Modified *Figure 8: "Capacitance variations"*, *Figure 9: "Normalized gate threshold voltage vs temperature"*, *Figure 10: "Normalized on-resistance vs temperature"*, *Figure 11: "Normalized $V_{(BR)DSS}$ vs temperature"* and *Figure 12: "Source-drain diode forward characteristics"*. Updated *Section 4: "Package information"*. Minor text changes.

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